

(19) (KR)
 (12) (B1)

(51) 。 Int. Cl. ⁷
 C09K 11/06
 (45) 2003 03 26
 (11) 10 - 0377321
 (24) 2003 03 11

(21) 10 - 2000 - 0082085 (65) 2001 - 0062711
 (22) 2000 12 26 (43) 2001 07 07

(30) 1019990067746 1999 12 31 (KR)

(73) 20

(72) 8 405

323

308 613

390 - 9301

247 - 184

388 - 11 301

(74)

:

(54) -

p -

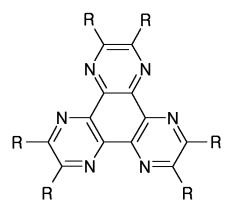
가

1

, ,

,

[1]



, R , , 1 12 , , ,

1

1

2

3

4

p -

11 21 , 12 22 , 13 , 14 , 15 25
 , 16 26 , 17 27 , 24 .

가 p -

p - (hole)
 가 , OPC (organic photo conductor drum)
 . (aryl amine)
 (blend)

(polycarbonate)

p -

p - 가
(exiton)
p - 가 , OPC
,

p -
 , (oligothiophene) (polythiophene) p - (thin
 film transistor) (carrier mobility)

가 , OPC , p - (Or
ganic Light Emitting Diode) , (oligothiophene)
가 .
가
(Adv. Mater. 12, 447, 2000). p - ,

r) p - (hole transporting layer) 2 가 (anode) . , (hole injecting layer)
가 .
가 .

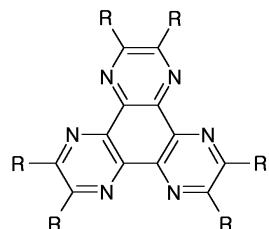
Copper phthalocyanine), 5,540,999 (oligothiophene) 가
 . 5,616,427 (quinacridone)

perature), , , (glass transition temp
(J. Appl. Phys. 84, 6859, 1998).

가 ,

1

[1]



R , 1 12 , , , , (aryla
mine), (ester), (amide), , , , (nitrile,
- CN)

1

1

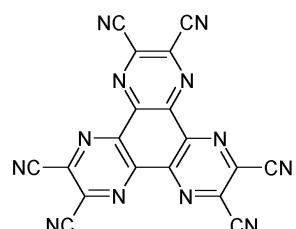
1

n -

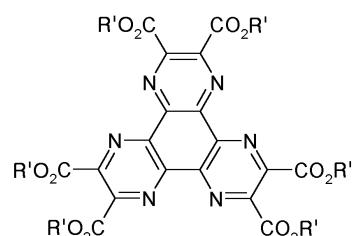
p -

1a. 1b. 1c. 1d

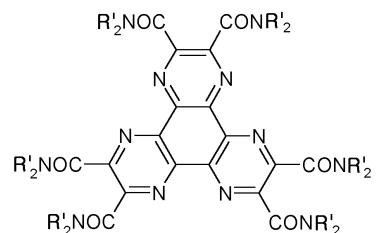
[1a]



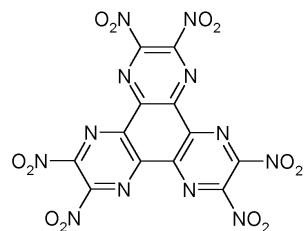
[1b]



[1c]



[1d]



, 1b 1c , R' (ester) (amide)
 , 1 15 , (phenyl), 3 15
 (spin-coating)

가

가

1

,

(12) , 1 (13), (11) (16), (1)
 7) (24), (25), 2 (26), (27) (14), (21), (22),
 가

가

1

,

,

(11, 21)

(wafer)

가

, , , , ,
], (polyaniline), (polypyrrole), PEDOT (poly[3,4 - (ethylene - 1,2 - dioxy)thiophene
 pant) 가 가 (polythiophene) (do

1 (13) 1 (Cop
 per phthalocyanine), (oligothiophene) p -
 0.1 10,000 nm 가 1 10 % 100 %
 , , , , 10 300 nm .

1 , p - , (mobility)가
가 .

Figure 1. 10 nm and 200 nm gold particles.

1 (13) (14)
 (polycyclic aromatic)
 4,4' - [N - (1 -) - N - -]
 (4,4' - bis[N - (1 - naphtyl) - N - phenyl - amino]biphenyl; NPB) ,

$$1 \qquad \qquad \qquad 2 \qquad \qquad \qquad (24)$$

(15, 25) (r)

ecomination) 8 -
 (8 - hydroxyquinoline aluminum salt; Alq₃), 5,366,811
 (dimerized styryl compound), (benzoxazole)
 (benzimidazole) , (p -) (poly(p - phenylene vinylene)), (copolymer) , (polyfluorene)

1 2 (16, 26) (17, 27)

1 , (photo voltaic cell;), , (gate insulator) OPC
 , (source) (drain) 1 p -

[]

1

1

1a

가

, , 1

ITO(indium tin oxide) 가 1500

5

ITO

1

1a

200

NPB(600)

5

1 /se

(LiF) 2500

c , 0.2 /sec,

3 7 /sec

3

2

1

1a

20

0 1000

가

3

3

1

1a

가

1

,

- (co - evaporation)
500

90 %

1a

200

10

1a

3

4

1

1a

가

1

,

- (co - evaporation)
500

70 %

1a

200

30

1a

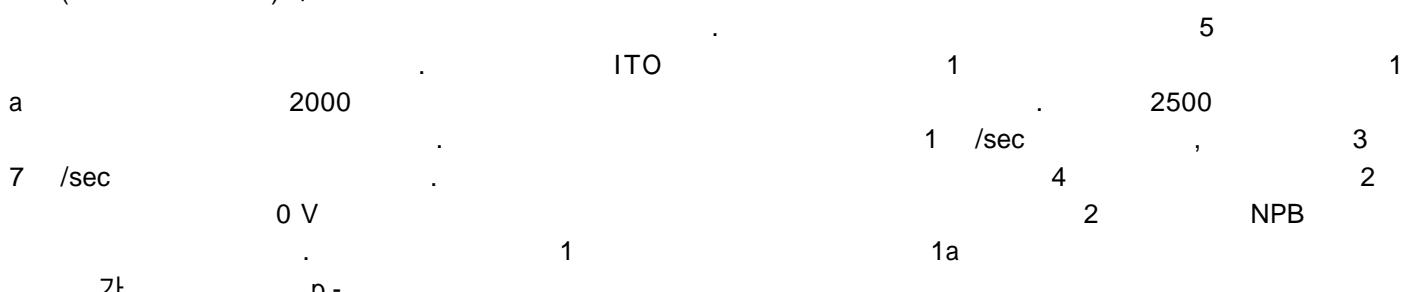
3

180

1

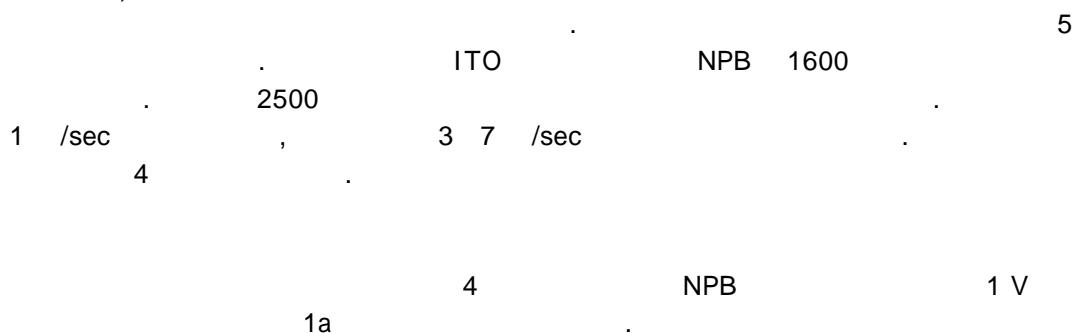
Figure 1a shows the current-voltage characteristics of the device. The current density (mA/cm^2) is plotted against voltage (V). The current density increases from 0 to approximately 150 mA/cm^2 at 0.5 V, then decreases to about 100 mA/cm^2 at 1.0 V, and remains relatively constant up to 1.5 V. The series resistance is calculated to be 93 Ω .

ITO(indium tin oxide)가 1500



2
7 1a 가 p - 가 ()
OPC 7 NPB

ITO(indium tin oxide)가 1500



1
가 , p -

1a
p -

가

1

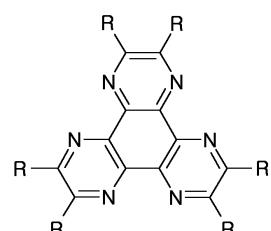
p -
가

(57)

1.

1

[1]



1 ,

R
ine), , (ester), , (amide), 1 12 , , , , (arylamin
- CN) . , (nitrile,

2.

1 ,

1 , , ,

3.

1 ,

a) ;

b) ;

c) ;

d) ;

e) ;

f) ;

g)

4.

1 ,

a) ;

b) ;

c) ;

e)

f) ;

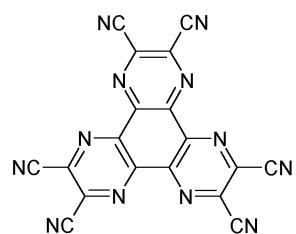
g)

5.

1 ,

1 1a :

[1a]

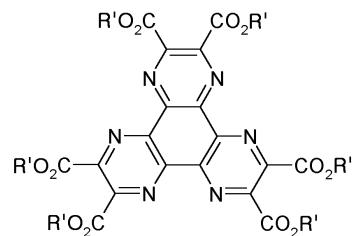


6.

1 ,

1b :

[1b]



1b , R'

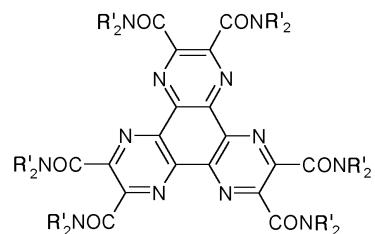
1 15 , (phenyl),

7.

1 ,

1c :

[1c]



1c , R'

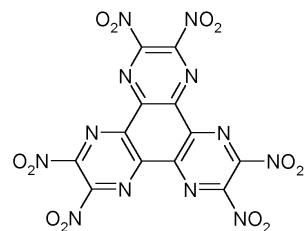
1 15 , (phenyl),

8.

1 ,

1d :

[1d]



9.

1 ,

1 ≥ 0.1 10,000 nm

10.

1 ,

1 , , , ,

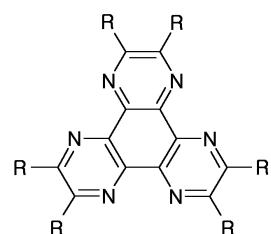
11.

1 4 ,

12.

1 , , ,

[1]



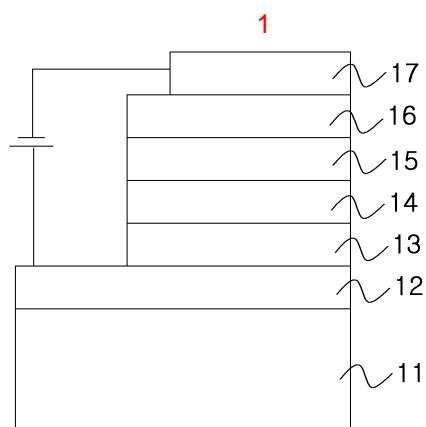
1 ,

R
ine), , 1 12 , , , , (arylam
(ester), (amide), , , , (nitrile, -
CN) .

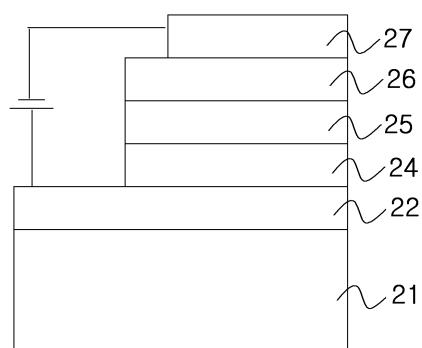
13.

12

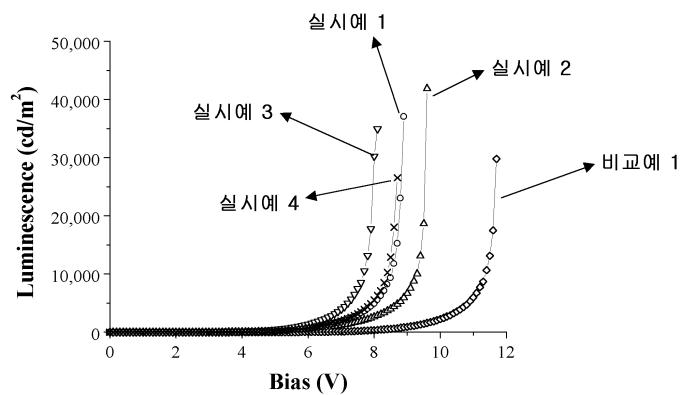
가 , , , (organic photo conductor; OPC)



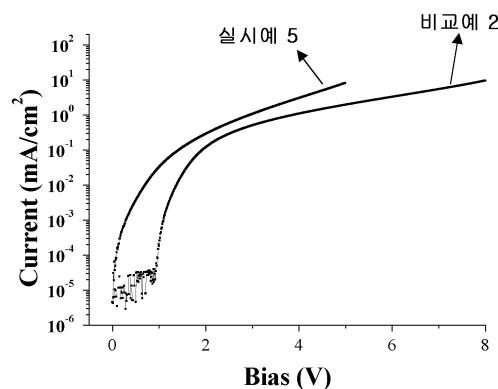
2



3



4



专利名称(译)	一种电子器件，包括具有p型半导体特性的有机化合物		
公开(公告)号	KR100377321B1	公开(公告)日	2003-03-26
申请号	KR1020000082085	申请日	2000-12-26
[标]申请(专利权)人(译)	乐金化学股份有限公司		
申请(专利权)人(译)	LG化学有限公司		
当前申请(专利权)人(译)	LG化学有限公司		
[标]发明人	SON SEHWAN 손세환 KIM OKHEE 김옥희 YOON SEOKHEE 윤석희 KIM KONGKYEOM 김공겸 LEE YOUNGU 이윤구 BAE JAESOON 배재순		
发明人	손세환 김옥희 윤석희 김공겸 이윤구 배재순		
IPC分类号	H01L51/50 C07D487/12 H01L51/30 H01L35/24 H01L51/52 C09K11/06 H01L51/05 C07D487/14 H01L51/42 C07D487/16 G03G5/06		
CPC分类号	H01L51/5012 H01L51/0072 H01L51/0545 Y10S428/917 H01L51/0076 H01L51/0055 H01L51/5203 C09B57/00 C07D487/14 H01L51/0562 H01L2251/308 H01L51/0081 Y02E10/549 Y10T428/31504		
代理人(译)	宋，BYEONG好		
优先权	1019990067746 1999-12-31 KR		
其他公开文献	KR1020010062711A		
外部链接	Espacenet		

摘要(译)

电子器件技术领域本发明涉及一种电子器件，其包括具有p型半导体特性并进行空穴注入或空穴传输作用的有机化合物。电子器件技术领域本发明涉及一种电子器件，其包括空穴注入层，空穴传输层和含有由下式(1)表示的有机化合物的空穴注入和传输层中的至少一种。可以降低驱动电压并且可以改善发射寿命。[化学式1]-1-每个R独立地或同时地是氢原子，具有1至12个碳原子的烃基，卤素基团，烷氧基，芳基胺基，酯基，酰胺基，芳香烃，十二烷基环化合物，硝基或腈基。。1指数方面有机发光器件，驱动电压，空穴，亮度，半导体，孔，型晶体管，太阳能电池，鸦片鼓

